

# Silicon Carbide (SiC) MOSFET – EliteSiC, 160 mohm, 1200 V, M1, TO-247-4L

## NTH4L160N120SC1

### Features

- Typ.  $R_{DS(on)}$  = 160 m $\Omega$
- Ultra Low Gate Charge ( $Q_{G(tot)}$  = 34 nC)
- High Speed Switching with Low Capacitance ( $C_{oss}$  = 49.5 pF)
- 100% Avalanche Tested
- $T_J$  = 175°C
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb-Free 2LI (on second level interconnection)

### Typical Applications

- UPS
- DC-DC Converter
- Boost Inverter

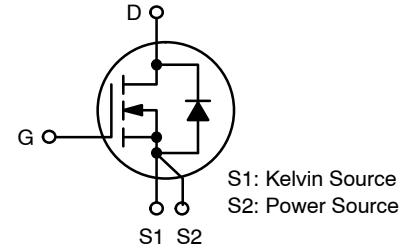
### MAXIMUM RATINGS ( $T_J$ = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	1200	V	
Gate-to-Source Voltage		$V_{GS}$	-15/+25	V	
Recommended Operation Values of Gate-to-Source Voltage		$T_C < 175^\circ\text{C}$ $V_{GSop}$	-5/+20	V	
Continuous Drain Current (Note 2)	Steady State	$T_C = 25^\circ\text{C}$	$I_D$	17.3	A
			$P_D$	111	W
Power Dissipation (Note 2)	Steady State	$T_C = 100^\circ\text{C}$	$I_D$	12.3	A
			$P_D$	55.5	W
Pulsed Drain Current (Note 3)	$T_A = 25^\circ\text{C}$		$I_{DM}$	69	A
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +175	°C	
Source Current (Body Diode)		$I_S$	11	A	
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)}$ = 16 A, L = 5 mH) (Note 4)		$E_{AS}$	128	mJ	
Maximum Lead Temperature for Soldering (1/8" from case for 5 s)		$T_L$	300	°C	

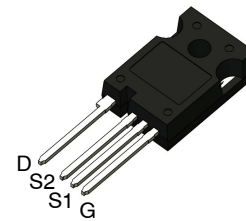
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1.  $J_A$  is constant value to follow guide table of LV/HV discrete final datasheet generation.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
3. Repetitive rating, limited by max junction temperature.
4.  $E_{AS}$  of 128 mJ is based on starting  $T_J = 25^\circ\text{C}$ ; L = 5 mH,  $I_{AS} = 16$  A,  $V_{DD} = 120$  V,  $V_{GS} = 18$  V.

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	$I_D$ MAX
1200 V	224 m $\Omega$ @ 20 V	17.3 A



N-CHANNEL MOSFET



TO-247-4LD  
CASE 340CJ

### MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Lot Traceability
- NTH4L160N120SC1 = Specific Device Code

### ORDERING INFORMATION

Device	Package	Shipping
NTH4L160N120SC1	TO-247-4LD	30 Units / Tube

# NTH4L160N120SC1

**Table 1. THERMAL RESISTANCE MAXIMUM RATINGS**

Parameter	Symbol	Max	Unit
Junction-to-Case – Steady State (Note 2)	$R_{\theta JC}$	1.35	°C/W
Junction-to-Ambient – Steady State (Notes 1, 2)	$R_{\theta JA}$	40	

**Table 2. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
<b>OFF CHARACTERISTICS</b>							
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	1200	-	-	V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 1\text{ mA}$ , referenced to $25^\circ\text{C}$	-	0.6	-	V/°C	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 1200\text{ V}$	$T_J = 25^\circ\text{C}$	-	-	100	$\mu\text{A}$
			$T_J = 175^\circ\text{C}$	-	-	1	mA
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = +25/-15\text{ V}, V_{DS} = 0\text{ V}$	-	-	$\pm 1$	$\mu\text{A}$	

**ON CHARACTERISTICS** (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 2.5\text{ mA}$	1.8	3.1	4.3	V
Recommended Gate Voltage	$V_{GOP}$		-5	-	+20	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 20\text{ V}, I_D = 12\text{ A}, T_J = 25^\circ\text{C}$	-	160	224	m $\Omega$
		$V_{GS} = 20\text{ V}, I_D = 12\text{ A}, T_J = 175^\circ\text{C}$	-	271	377	
Forward Transconductance	$g_{FS}$	$V_{DS} = 20\text{ V}, I_D = 12\text{ A}$	-	3.2	-	S

**CHARGES, CAPACITANCES & GATE RESISTANCE**

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 800\text{ V}$	-	665	-	pF
Output Capacitance	$C_{OSS}$		-	49.5	-	
Reverse Transfer Capacitance	$C_{RSS}$		-	4.3	-	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -5/20\text{ V}, V_{DS} = 600\text{ V}, I_D = 16\text{ A}$	-	34	-	nC
Threshold Gate Charge	$Q_{G(TH)}$		-	6	-	
Gate-to-Source Charge	$Q_{GS}$		-	12.5	-	
Gate-to-Drain Charge	$Q_{GD}$		-	9.6	-	
Gate-Resistance	$R_G$	$f = 1\text{ MHz}$	-	1.4	-	$\Omega$

**SWITCHING CHARACTERISTICS,  $V_{GS} = 10\text{ V}$**

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -5/20\text{ V}, V_{DS} = 800\text{ V}, I_D = 16\text{ A}, R_G = 6\text{ }\Omega$ Inductive load	-	11	20	ns
Rise Time	$t_r$		-	10	20	
Turn-Off Delay Time	$t_{d(OFF)}$		-	14	25	
Fall Time	$t_f$		-	7	14	
Turn-On Switching Loss	$E_{ON}$		-	104	-	$\mu\text{J}$
Turn-Off Switching Loss	$E_{OFF}$		-	32	-	
Total Switching Loss	$E_{tot}$		-	136	-	

**DRAIN-SOURCE DIODE CHARACTERISTICS**

Continuous Drain-Source Diode Forward Current	$I_{SD}$	$V_{GS} = -5\text{ V}, T_J = 25^\circ\text{C}$	-	-	11	A
Pulsed Drain-Source Diode Forward Current (Note 3)	$I_{SDM}$		-	-	69	
Forward Diode Voltage	$V_{SD}$	$V_{GS} = -5\text{ V}, I_{SD} = 6\text{ A}, T_J = 25^\circ\text{C}$	-	4	-	V
Reverse Recovery Time	$t_{RR}$	$V_{GS} = -5/20\text{ V}, I_{SD} = 16\text{ A}, dI_S/dt = 1000\text{ A}/\mu\text{s}$	-	15	-	ns
Reverse Recovery Charge	$Q_{RR}$		-	47	-	nC

# NTH4L160N120SC1

**Table 2. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise specified) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>						
Reverse Recovery Energy	$E_{REC}$	$V_{GS} = -5/20\text{ V}$ , $I_{SD} = 16\text{ A}$ , $di_S/dt = 1000\text{ A}/\mu\text{s}$	-	3.9	-	$\mu\text{J}$
Peak Reverse Recovery Current	$I_{RRM}$		-	6.6	-	A
Charge Time	$T_a$		-	7.0	-	ns
Discharge Time	$T_b$		-	7.4	-	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# NTH4L160N120SC1

## TYPICAL CHARACTERISTICS

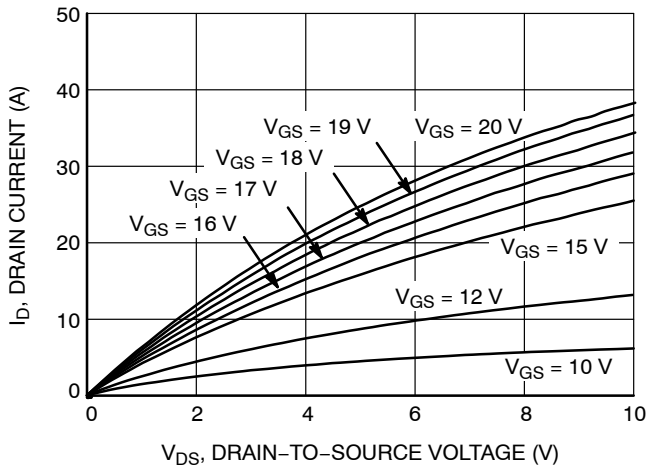


Figure 1. On Characteristics

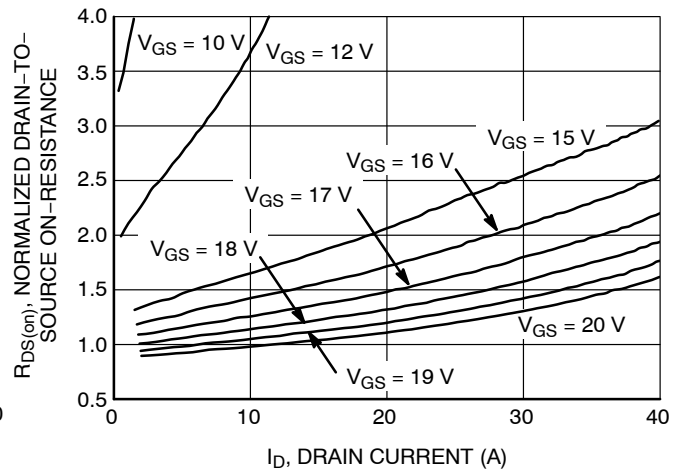


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

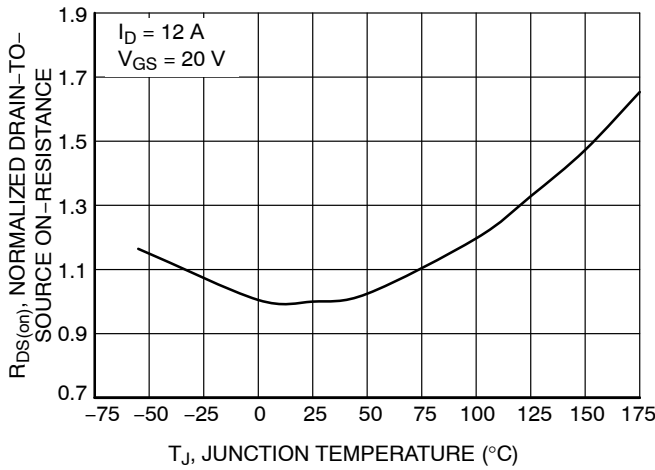


Figure 3. On-Resistance Variation with Temperature

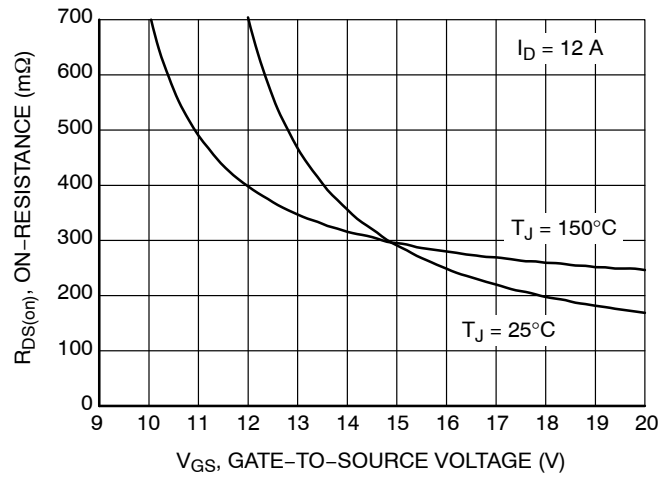


Figure 4. On-Resistance vs. Gate-to-Source Voltage

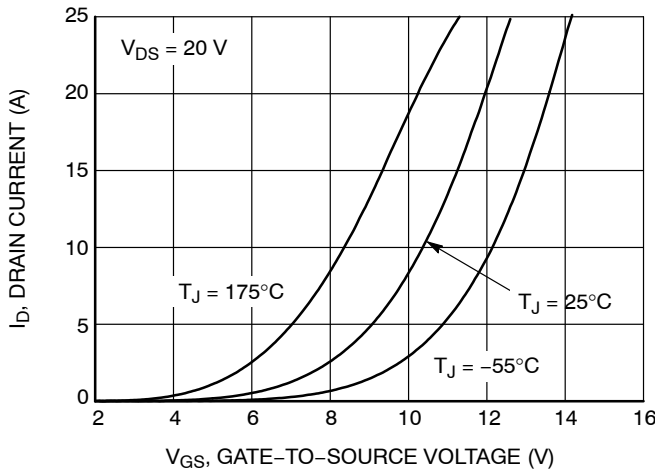


Figure 5. Transfer Characteristics

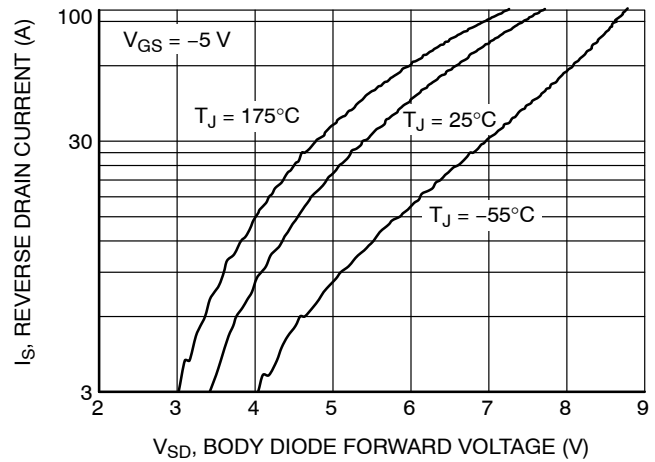
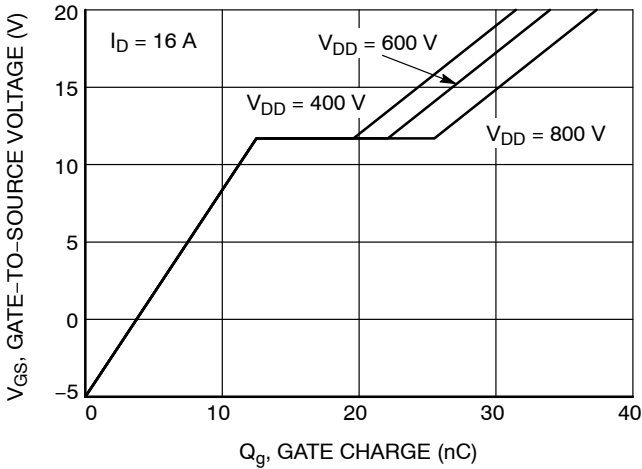


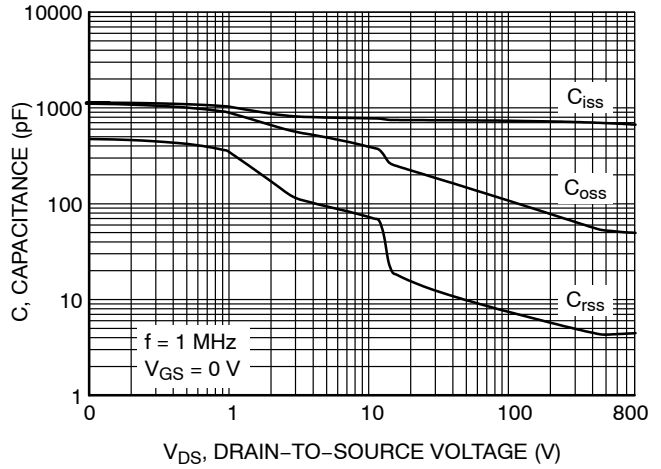
Figure 6. Diode Forward Voltage vs. Current

# NTH4L160N120SC1

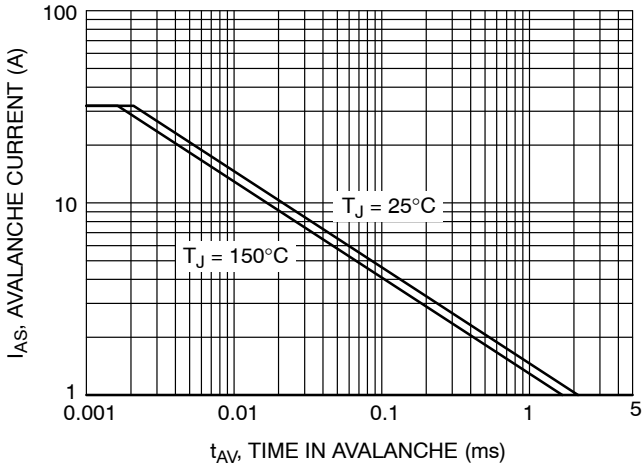
## TYPICAL CHARACTERISTICS (CONTINUED)



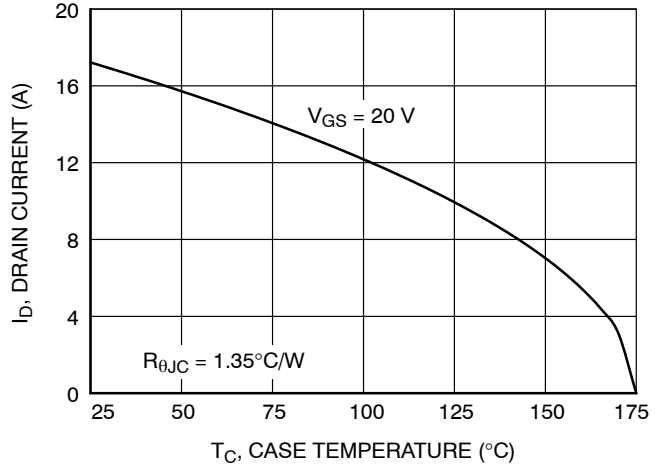
**Figure 7. Gate-to-Source Voltage vs. Total Charge**



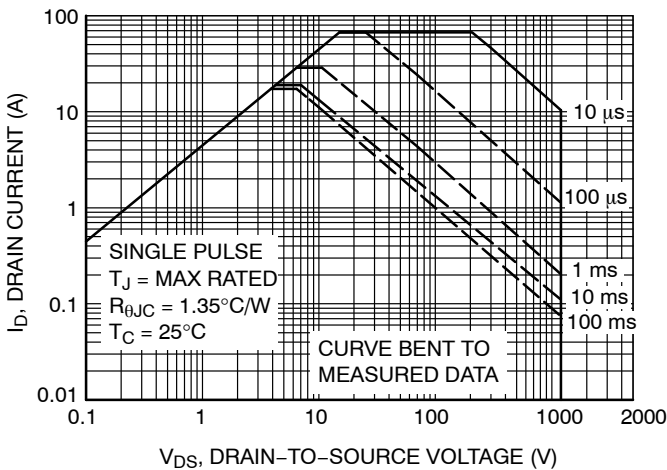
**Figure 8. Capacitance vs. Drain-to-Source Voltage**



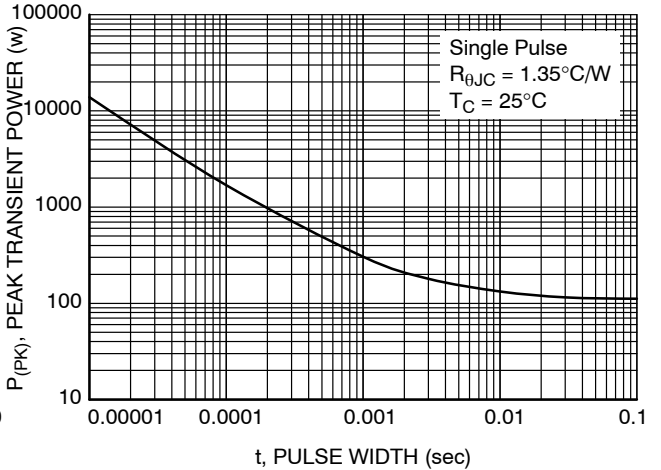
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**



**Figure 11. Maximum Rated Forward Biased Safe Operating Area**



**Figure 12. Single Pulse Maximum Power Dissipation**

# NTH4L160N120SC1

## TYPICAL CHARACTERISTICS (CONTINUED)

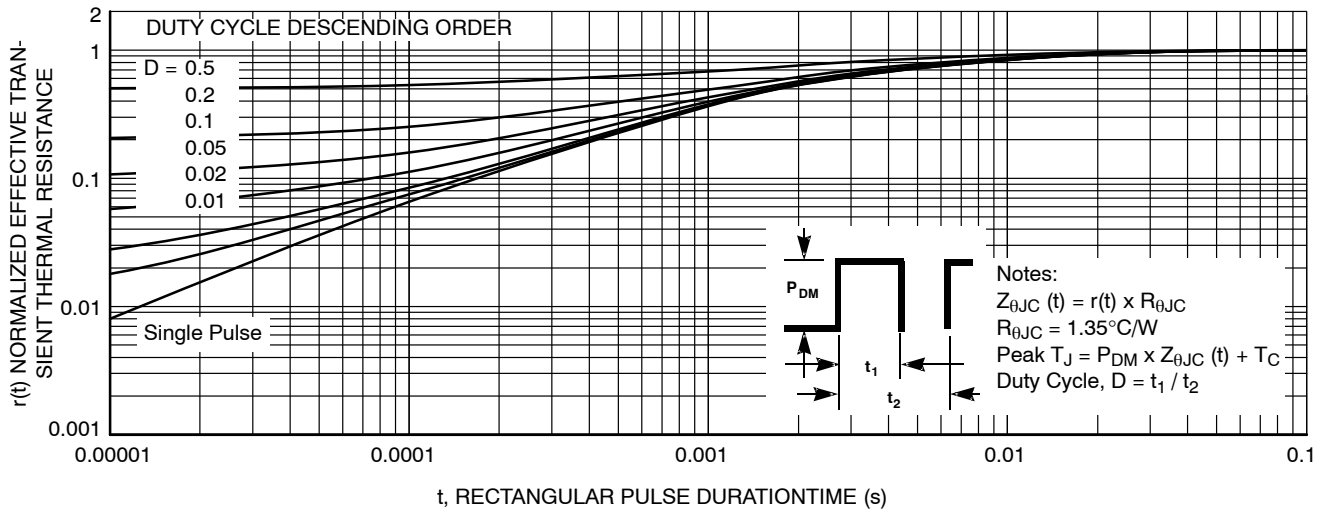


Figure 13. Junction-to-Case Transient Thermal Response Curve

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



TO-247-4LD  
CASE 340CJ  
ISSUE A

DATE 16 SEP 2019



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.10	2.40	2.70
A2	1.80	2.00	2.20
b	1.07	1.20	1.33
b1	1.20	1.40	1.60
b2	2.02	2.22	2.42
c	0.50	0.60	0.70
D	22.34	22.54	22.74
D1	16.00	16.25	16.50
D2	0.97	1.17	1.37
e	2.54 BSC		
e1	5.08 BSC		
E	15.40	15.60	15.80
E1	12.80	13.00	13.20
E/2	4.80	5.00	5.20
L	18.22	18.42	18.62
L1	2.42	2.62	2.82
p	3.40	3.60	3.80
p1	6.60	6.80	7.00
Q	5.97	6.17	6.37
S	5.97	6.17	6.37

NOTES:

- A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5-2009.

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